2-input NAND gate Rev. 06 — 30 May 2007

1. General description

74AHC1G00 and 74AHCT1G00 are high-speed Si-gate CMOS devices. They provide a 2-input NAND function.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- ESD protection:
 - HBM JESD22-A114E: exceeds 2000 V
 - MM JESD22-A115-A: exceeds 200 V
 - CDM JESD22-C101C: exceeds 1000 V
- Specified from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AHC1G00GW 74AHCT1G00GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1					
74AHC1G00GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753					
74AHCT1G00GV									

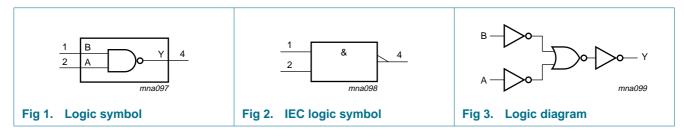


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4. Marking

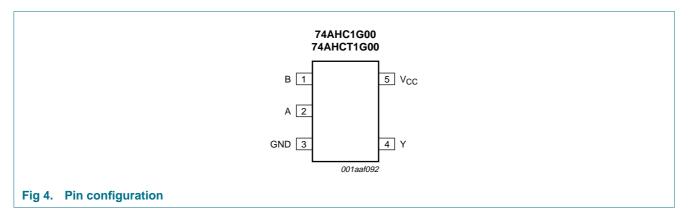
Table 2. Marking codes	
Type number	Marking
74AHC1G00GW	AA
74AHC1G00GV	A00
74AHCT1G00GW	CA
74AHCT1G00GV	C00

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
В	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

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7. Functional description

Table 4. Function table

H = *HIGH* voltage level; *L* = *LOW* voltage level

Inputs		Output
Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{\rm I} < -0.5 ~\rm V$	-20	-	mA
Ι _{ΟΚ}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For both TSSOP5 and SC-74A packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74	74AHC1G00			74AHCT1G00		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	V_{CC} = 3.3 V \pm 0.3 V	-	-	100	-	-	-	ns/V
	and fall rate	$V_{CC}=5.0~V\pm0.5~V$	-	-	20	-	-	20	ns/V

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10. Static characteristics

Table 7.Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		−40 °C	to +85 °C	–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
For type	74AHC1G00									
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
VIL	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level	$V_I = V_{IH} \text{ or } V_{IL}$								
	output voltage	I_{O} = -50 μ A; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O} = -50 \ \mu\text{A}; \ V_{CC} = 3.0 \ \text{V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = 50 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_0 = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_0 = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
l	input leakage current	$V_I = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current		-	-	1.0	-	10	-	40	μΑ
CI	input capacitance		-	1.5	10	-	10	-	10	pF
For type	74AHCT1G00									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 V$								
	output voltage	I _O = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		l _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
lı	input leakage current	$V_{I} = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μΑ

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Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions		25 °C		−40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	1
I _{CC}	supply current		-	-	1.0	-	10	-	40	μA
∆l _{CC}	additional supply current	per input pin; V _I = 3.4 V; other inputs at V _{CC} or GND; $I_O = 0 A$; V _{CC} = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
CI	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f = \le 3.0$ ns. For test circuit see <u>Figure 6</u>.

Symbol	Parameter	Conditions			25 °C		_40 °C 1	to +85 °C	_40 °C t	to +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	1
For type	74AHC1G00										
	propagation	A and B to Y; see Figure 5	[1]								
	delay	V_{CC} = 3.0 V to 3.6 V	[2]								
		C _L = 15 pF		-	4.5	7.9	1.0	9.5	1.0	10.5	ns
		C _L = 50 pF		-	6.5	11.4	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	3.5	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		-	4.9	7.5	1.0	8.5	1.0	9.5	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; \text{ f} = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	17	-	-	-	-	-	pF
For type	74AHCT1G0	0									
t _{pd}	propagation delay	A and B to Y; see <u>Figure 5;</u> V _{CC} = 4.5 V to 5.5 V	[1] [3]								
		C _L = 15 pF		-	3.6	6.2	1.0	7.1	1.0	8.0	ns
		C _L = 50 pF		-	5.0	7.9	1.0	9.0	1.0	10.0	ns
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC}	<u>[4]</u>	-	18	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] Typical values are measured at V_{CC} = 3.3 V.

[3] Typical values are measured at $V_{CC} = 5.0$ V.

[4] C_{PD} is used to determine the dynamic power dissipation P_D (μ W).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in Volts.

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12. Waveforms

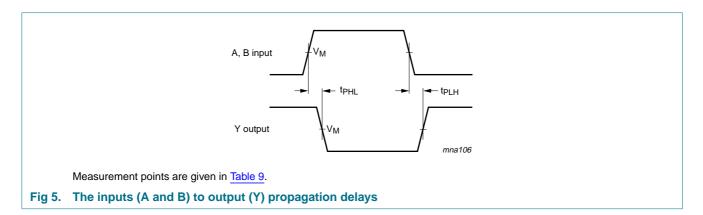
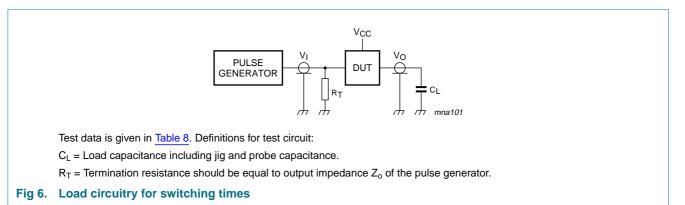


Table 9.Measurement point

Туре	Input	Output	
	VI	V _M	V _M
74AHC1G00	GND to V _{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT1G00	GND to 3.0 V	1.5 V	$0.5 \times V_{CC}$



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13. Package outline

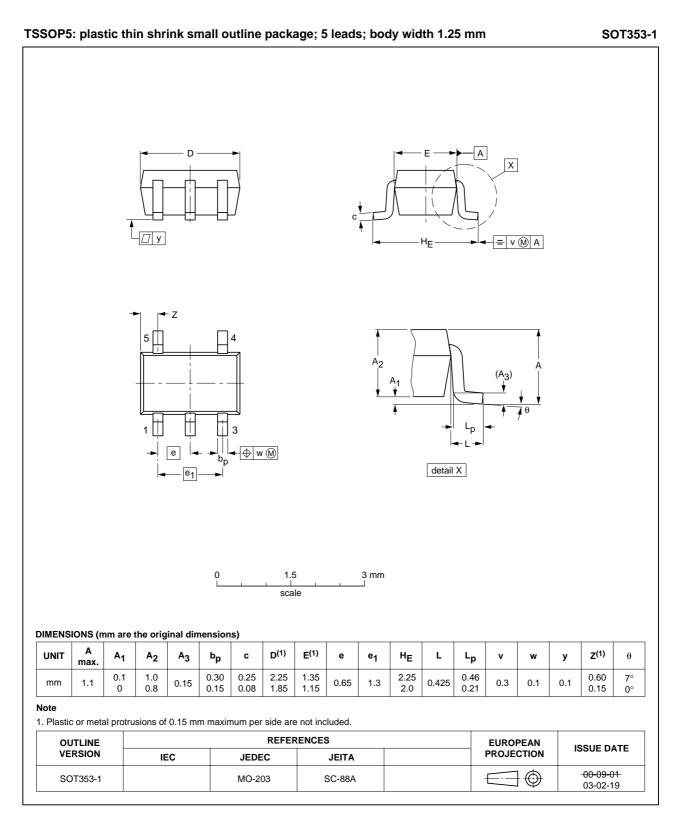


Fig 7. Package outline SOT353-1 (TSSOP5)

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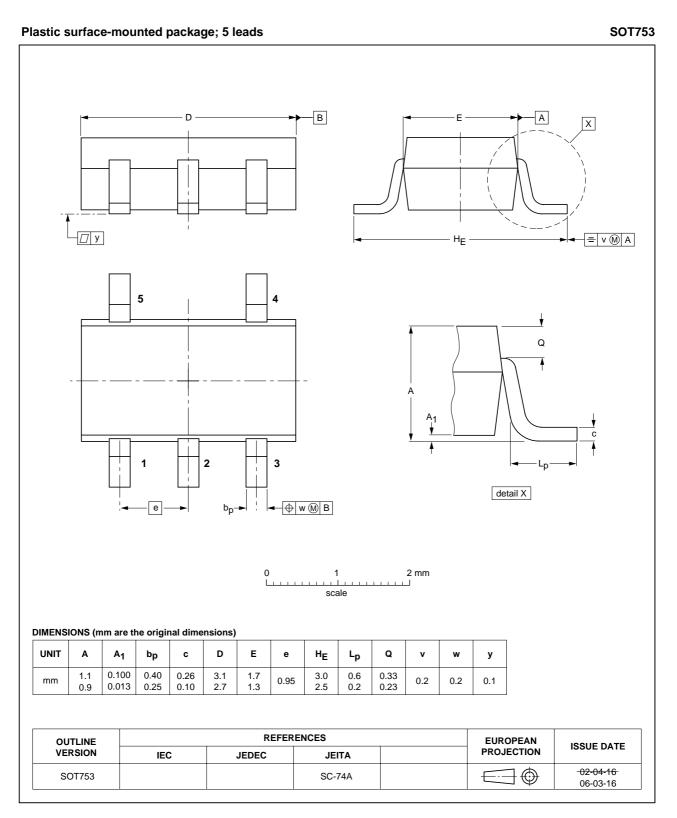


Fig 8. Package outline SOT753 (SC-74A)

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14. Abbreviations

Table 10.	Abbreviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

	-						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
74AHC_AHCT1G00_6	20070530	Product data sheet	-	74AHC_AHCT1G00_5			
Modifications: • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.							
	 Legal texts h 	ave been adapted to the new o	company name wher	re appropriate.			
	 Package SO⁻ 	T353 changed to SOT353-1 in	Section 3 and Section	<u>on 13</u> .			
	 Quick reference 	nce data and Soldering section	is removed.				
74AHC_AHCT1G00_5	20020527	Product specification	-	74AHC_AHCT1G00_4			
74AHC_AHCT1G00_4	20020227	Product specification	-	74AHC_AHCT1G00_3			
74AHC_AHCT1G00_3	20010131	Product specification	-	74AHC_AHCT1G00_2			
74AHC_AHCT1G00_2	19990127	Product specification	-	74AHC_AHCT1G00_N_1			
74AHC_AHCT1G00_N_1	19981125	Preliminary specification	-	-			

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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